

IN THE CLAIMS:

Please amend claims 1-3 and 6-10 as follows:

Listing of Claims:

Claim 1 (Currently Amended): A method for measuring a dielectric constant of a thin film sample, comprising:

irradiating ~~[[a]]~~ the thin film sample with light at a first incident angle, whereby the light undergoes multiple internal reflections within the thin film sample;

measuring light that has transmitted through or reflected on the thin film sample following said multiple internal reflections; and

determining a complex dielectric constant of the thin film sample based upon a spectrum of the transmitted or reflected light that has undergone said multiple internal reflections.

Claim 2 (Currently Amended): The method according to claim 1, wherein a complex dielectric constant of the thin film sample is determined by setting an incident angle of the incident light upon the thin film sample at 60 degrees or greater and smaller than 90 degrees.

Claim 3 (Currently Amended): The method according to claim 1, wherein the thin film sample is a substrate having a uniform dielectric constant and uniform thickness or the thin film sample having a thin film provided on a part of the substrate.

Claim 4 (Previously Presented): The method according to claim 1, wherein the irradiation light is S-polarized light.

Claim 5 (Previously Presented): The method according to claim 1, wherein the irradiation light has a wavelength in a region of a millimeter wave, a sub-millimeter wave or a tera-hertz frequency range of light.

Claim 6 (Currently Amended): An apparatus for measuring a complex dielectric constant of a thin film sample by irradiating the sample with light, comprising:

light irradiating unit that irradiates the thin film sample with light at a first incident angle, whereby the light undergoes multiple internal reflections within the thin film sample;

measuring unit that measures light transmitted through or reflected upon the thin film sample following said multiple internal reflections; and

determining unit that determines a complex dielectric constant of the thin film sample based upon a spectrum of the transmitted or reflected light that has undergone said multiple internal reflections.

Claim 7 (Currently Amended): The apparatus according to claim 6, wherein incident light upon the thin film sample is changeable in the position, and a photodetector for receiving the transmitted or reflected light is also changeable in the position.

Claim 8 (Currently Amended): The apparatus according to claim 6, wherein incident light upon the thin film sample is changeable in incident angle.

Claim 9 (Currently Amended): The apparatus according to claim 7, wherein incident light upon the thin film sample is changeable in incident angle.

Claim 10 (Currently Amended): The method according to claim 2, wherein the thin film sample is a substrate having a uniform dielectric constant and uniform thickness or the thin film sample having a thin film provided on a part of the substrate.

Claim 11 (Previously Presented): The method according to claim 2, wherein the irradiation light has a wavelength in a region of a millimeter wave, a sub-millimeter wave or a tera-hertz frequency range of light.

Claim 12 (Previously Presented): The method according to claim 3, wherein the irradiation light has a wavelength in a region of a millimeter wave, a sub-millimeter wave or a tera-hertz frequency range of light.